

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
26 February 2004 (26.02.2004)

PCT

(10) International Publication Number
WO 2004/017378 A2

- (51) International Patent Classification⁷: **H01L**
- (21) International Application Number:
PCT/US2003/025739
- (22) International Filing Date: 18 August 2003 (18.08.2003)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
60/404,371 18 August 2002 (18.08.2002) US
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(81) Designated States (national): AE, AG, AL, AM, AT, AU,
AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU,
CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,
GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC,
LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,
MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC,
SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA,
UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

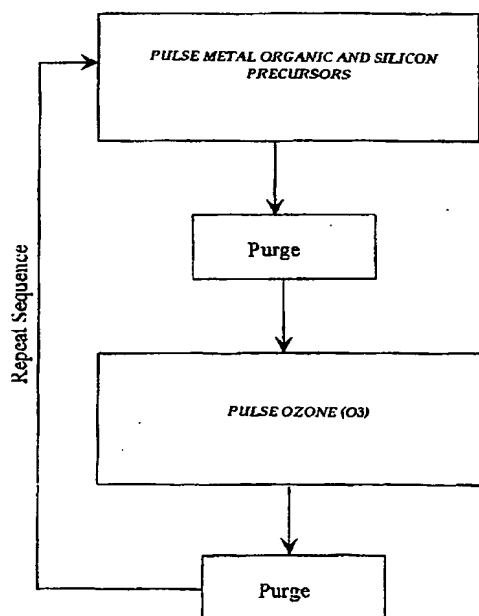
(84) Designated States (regional): ARIPO patent (GH, GM,
KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),
Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE,
ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO,
SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM,
GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— without international search report and to be republished
upon receipt of that report

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: ATOMIC LAYER DEPOSITION OF HIGH K METAL SILICATES



(57) Abstract: The present invention relates to the atomic layer deposition ("ALD") of high k dielectric layers of metal silicates, including hafnium silicate. More particularly, the present invention relates to the ALD formation of metal silicates using metal organic precursors, silicon organic precursors and ozone. Preferably, the metal organic precursor is a metal alkyl amide and the silicon organic precursor is a silicon alkyl amide.

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